

Excellent Integrated System Limited

Stocking Distributor

Click to view price, real time Inventory, Delivery & Lifecycle Information:

[Panasonic Electronic Components](#)

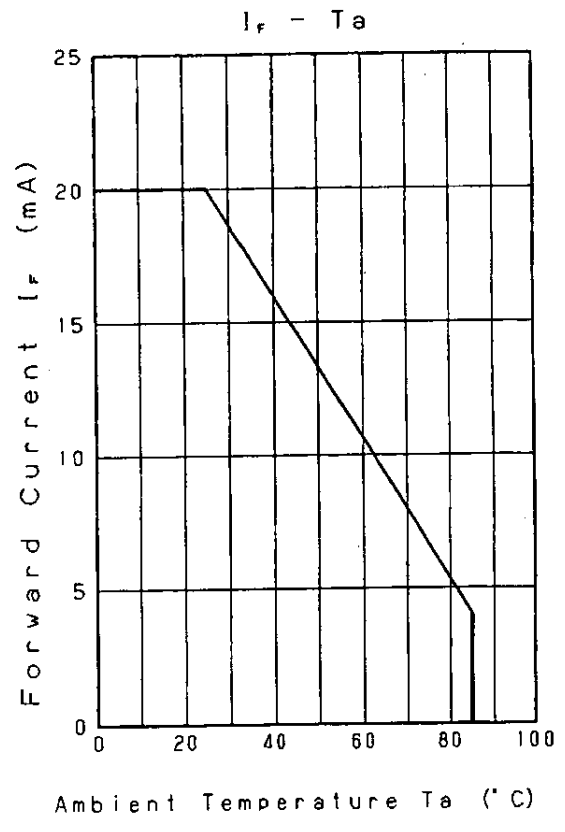
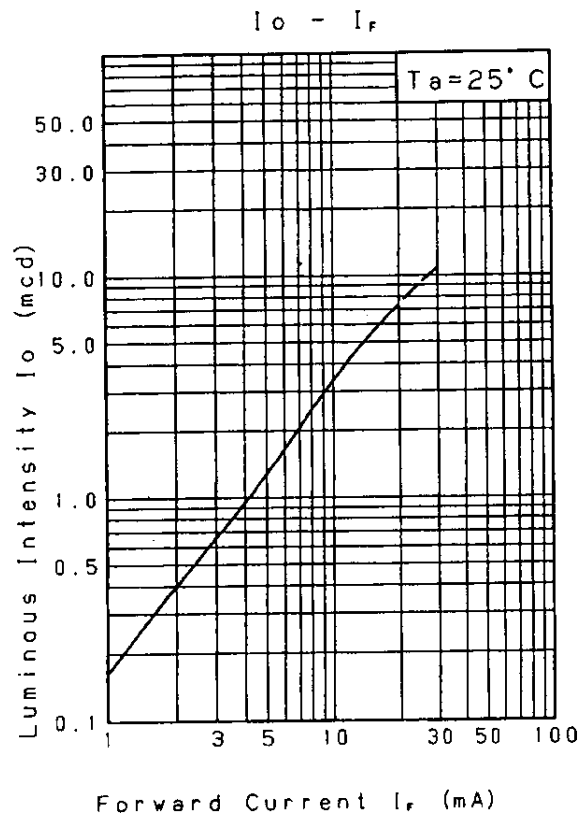
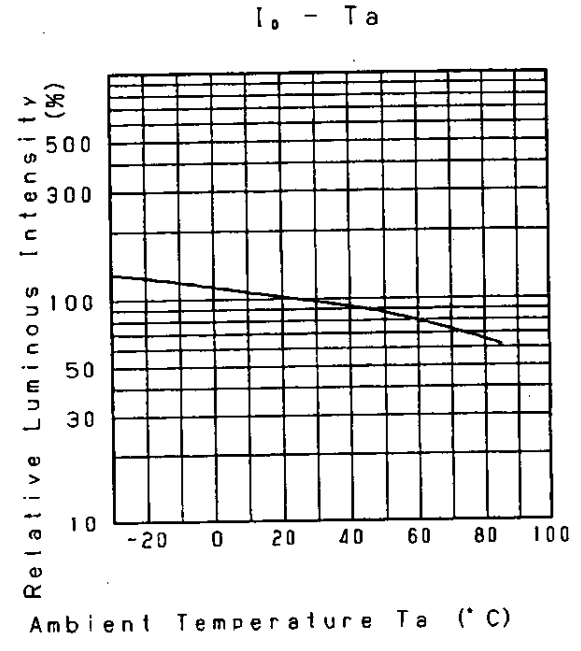
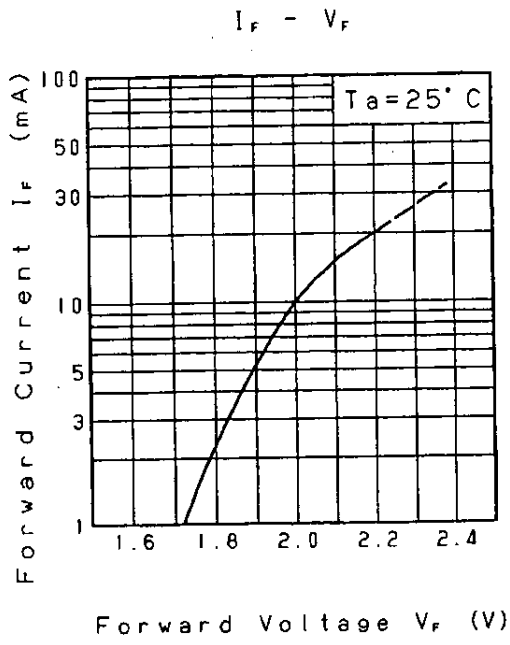
[LNJ416Q8YRA](#)

For any questions, you can email us directly:

sales@integrated-circuit.com

Approved	Checked	Designed	DEVELOPMENT SPECIFICATION							
<i>T. Akada</i>	<i>M. Ni</i>	<i>T. Takata</i>	P/N: LNJ416Q8YRA							
T	Y	P	E	Amber Light Emitting Diode						
APPLICATION			Indicators							
MATERIAL			GaAs?							
OUTLINE			Attached							
ABSOLUTE MAXIMUM RATINGS			P	※ I _{FP}	I _{FDC}	V _R	Topr	Tstg		
			60	100	20	4	-30~+85	-40~+100		
			mW	mA	mA	V	°C	°C		
CONDITION			Ta=25±3°C							
Test Specification										
Item	Symbol	Condition	Typ	Limit		Unit				
				Min	Max					
Forward Voltage	V _F	I _F =10 mA	2.0		2.6	V				
Reverse Leakage Current	I _R	V _R = 4 V			10	μA				
Luminous Intensity	I _O	I _F =10 mA · DC	3.3	1.2		mcd				
Peak Emission Wavelength	λ _p	I _F =10 mA · DC	590			nm				
Spectral Line Half Width	Δλ	I _F =10 mA · DC	30			nm				
※ · The Condition of I _{FP} is duty 10 %. Pulse width 1 ms · Please contact the Panasonic local office if you design at low current (below 1 mA DC) or pulse current operation and have any questions.										
NOTE 1. Soldering conditions. Refer to Handling note. 2. Care should be taken that soldering is done within 3-days after opening the dry package and reel. 3. Compositions of the lead····Cu/Ni/Au plating 4. Lens : Yellow clear type										
Jan. 31. 2000										

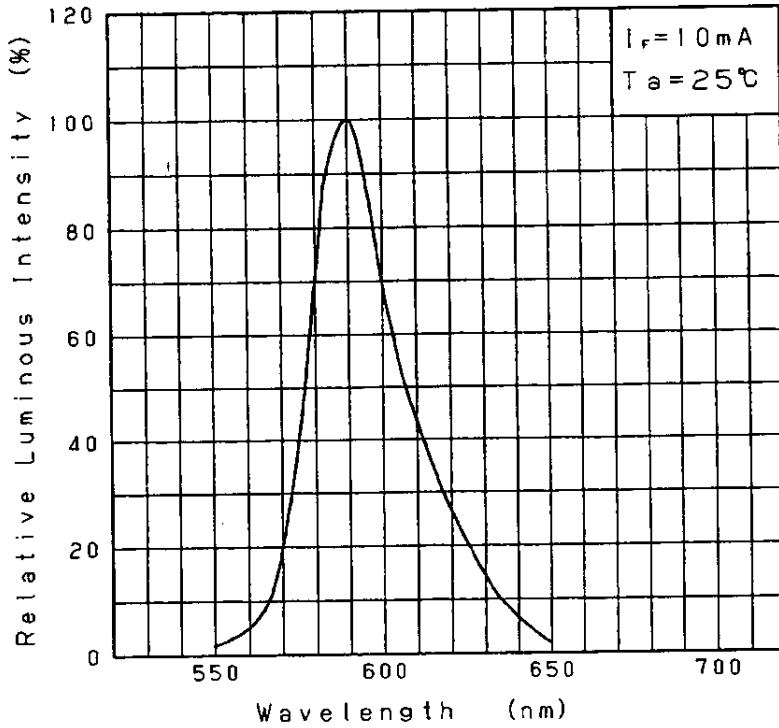
Approved	Checked	Designed	DEVELOPMENT SPECIFICATION		
T. Shoda	h. hi	T. Tadate	P/N: LNJ416Q8YRA		



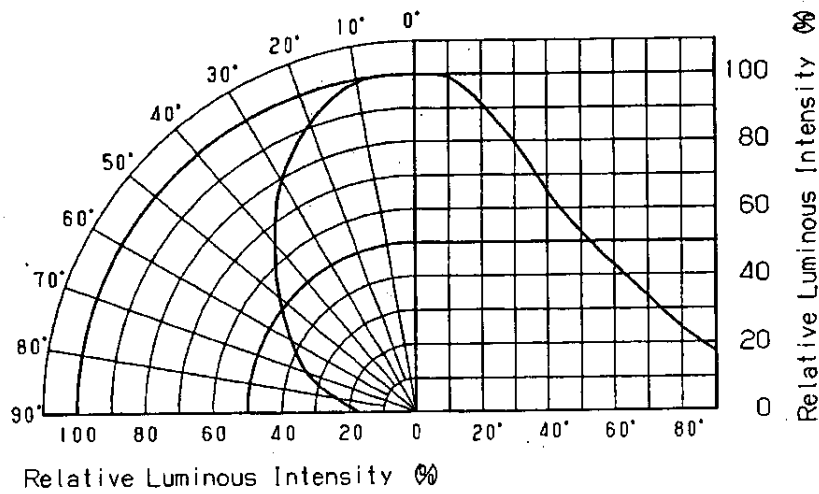
Jan. 31. 2000		

Approved	Checked	Designed	DEVELOPMENT SPECIFICATION		
<i>T. Akada</i>	<i>M. Hara</i>	<i>T. Tabata</i>	P/N: LNJ416Q8YRA		

Relative Luminous Intensity
Wavelength Characteristics



Directive Characteristics



Jan. 31. 2000			
---------------	--	--	--

